

REMARKS

Applicants note with appreciation the Examiner's allowance of claims 1-3, 5, 6, 17, 18 and 21-26. Applicants, however, submit the following comments regarding the Examiner's Reasons for Allowance stated on Page 2 of the Notice of Allowance. In the Reasons for Allowance, the Examiner indicated that the prior art of record fails to teach "a memory device and a method of forming thereof" that includes "a first pair of fins including a first fin and a second fin formed substantially parallel to one another and located a distance d from one another, a second pair of fins including a third fin and a fourth fin formed substantially parallel to one another and located the distance d from one another, the second fin being formed substantially parallel to the third fin and located a distance approximately twice the distance d from the third fin, a source region and a drain region formed at ends of each of the fins, a gate formed over the first fin and the second fin, and characterized in that either each of the fins has a width that is approximately half of the distance d or that the first and third fins are doped with n-type impurities and the second and fourth fins are doped with p-type impurities."

This statement of reasons for allowance appears to combine different features from each of independent claims 1, 17 and 24. Applicants note, however, that each of claims 1, 17 and 24, independently, recite a combination of features not suggested or disclosed by the references of record. For example, claim 1 recites the following combination of features: "a memory device, comprising: a first pair of fins comprising a first fin and a second fin formed substantially parallel to one another, the first fin and second fin having a first width and being located a distance from one another that is approximately twice the first width; a second pair

of fins comprising a third fin and a fourth fin formed substantially parallel to one another, the third fin and fourth fin having the first width and being located a distance from one another that is approximately twice the first width, wherein the second fin and the third fin are formed substantially parallel to one another and located a distance from one another that is approximately four times the first width; a source region formed at one end of each of the fins; a drain region formed at an opposite end of each of the fins; a gate formed over the first fin and the second fin; a wordline formed over each of the fins; and a bitline contact formed adjacent at least one of the fins.”

Furthermore, claim 17 recites the following combination of features: “a method for forming a memory device, comprising: forming a first fin and a second fin substantially parallel to one another and to each have a first width and to be located a distance from one another that is approximately twice the first width; forming a third fin and a fourth fin substantially parallel to one another and to each have the first width and to be located a distance from one another that is approximately twice the first width and such that the second fin and the third fin are substantially parallel to one another and located a distance from one another that is approximately four times the first width; forming a source region at one end of each of the fins; forming a drain region at an opposite end of each of the fins; forming a gate over the first fin and the second fin; forming a wordline over each of the fins; and forming a bitline contact adjacent at least one of the fins.


Additionally, claim 24 recites the following combination of features: “a device, comprising: a first fin and a second fin formed substantially parallel to one another and located approximately a distance d from one another; a third fin and a fourth fin formed

substantially parallel to one another and located approximately the distance d from one another, wherein the second fin is formed substantially parallel to the third fin and is located approximately twice the distance d from the third fin and wherein the first and third fins are doped with n-type impurities and the second and fourth fins are doped with p-type impurities; a source region formed at one end of each of the first, second, third and fourth fins; a drain region formed at an opposite end of each of the first, second, third and fourth fins; and a gate formed over the first and second fins.

Applicants submit that it is the novel and non-obvious combination of features recited in each of claims 1, 17 and 24, independently, that distinguish these claims over the references of record.

To the extent necessary, a petition for an extension of time under 37 CFR § 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account No. 50-1070 and please credit any excess fees to such deposit account.

Respectfully submitted,

A handwritten signature in black ink that reads "Tony M. Cole". The signature is written in a cursive style with a large initial "T".

By: _____
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